

## KSE170/171/172

Low Power Audio Amplifier
Low Current, High Speed Switching Applications



## PNP Epitaxial Silicon Transistor

1. Emitter 2.Collector 3.Base

### Absolute Maximum Ratings T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter		Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	: KSE170	- 60	V
		: KSE171	- 80	V
	- 500	: KSE172	- 100	V
V <sub>CEO</sub>	Collector-Emitter Voltage	: KSE170	- 40	V
	THE COM	: KSE171	- 60	V
	2750.00	: KSE172	- 80	V
V <sub>EBO</sub>	Emitter-Base Voltage		- 7	V
Ic	Collector Current (DC)		- 3	Α
I <sub>CP</sub>	Collector Current (Pulse)		- 6	Α
	Base Current		- 1	Α
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)		12.5	W
	Collector Dissipation (T <sub>a</sub> =25°C)		1.5	W
TJ	Junction Temperature		150	°C
T <sub>STG</sub>	Storage Temperature	/ 90. WAT	- 65 ~ 150	°C

### Electrical Characteristics T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV <sub>CEO</sub>	Collector-Emitter Breaksown Voltage : KSE170 : KSE171	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0	-40 -60		V
	: KSE171		-80		V
I <sub>CBO</sub>	Collector Cut-off Current : KSE170 : KSE171 : KSE172	V <sub>CB</sub> = -60V, I <sub>B</sub> = 0 V <sub>CB</sub> = -80V, I <sub>E</sub> = 0 V <sub>CB</sub> = -100V, I <sub>E</sub> = 0	<b>.</b> =	-0.1 -0.1 -0.1	μΑ μΑ μΑ
	: KSE172 : KSE170 : KSE171 : KSE172	V <sub>CB</sub> = -100V, I <sub>E</sub> = 0 V <sub>CB</sub> = -60V, I <sub>E</sub> = 0, T <sub>C</sub> = 150°C V <sub>CB</sub> = -80V, I <sub>E</sub> = 0, T <sub>C</sub> = 150°C V <sub>CB</sub> = -100V, I <sub>E</sub> = 0, T <sub>C</sub> = 150°C	NWW	-0.1 -0.1 -0.1 -0.1	mA mA mA
I <sub>EBO</sub>	Emitter Cut-off Current	V <sub>BE</sub> = - 7V, I <sub>C</sub> = 0		-0.1	μΑ
h <sub>FE</sub>	DC Current Gain	V <sub>CE</sub> = -1V, I <sub>C</sub> = -100mA V <sub>CE</sub> = -1V, I <sub>C</sub> = -500mA V <sub>CE</sub> = -1V, I <sub>C</sub> = -1.5A	50 30 12	250	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	$I_C = -500$ mA, $I_B = -50$ mA $I_C = -1.5$ A, $I_B = -150$ mA $I_C = -3$ A, $I_B = -600$ mA		-0.3 -0.9 -1.7	V V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> = - 1.5A, I <sub>B</sub> = - 150mA I <sub>C</sub> = - 3A, I <sub>B</sub> = - 600mA		-1.5 -2.0	V
V <sub>BE</sub> (on)	Base-Emitter On Voltage	V <sub>CE</sub> = - 1V, I <sub>C</sub> = - 500mA		-1.2	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> = - 10V, I <sub>C</sub> = - 100mA	50		MHz
D C <sub>ob</sub>	Output Capacitance	$V_{CB} = -10V, I_{E} = 0, f = 0.1MHz$		50	pF

## **Typical Charactristics**

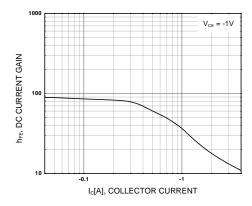


Figure 1. DC current Gain

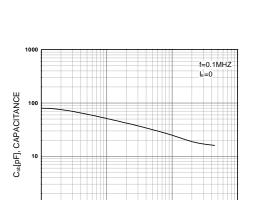


Figure 3. Collector Output Capacitance

 $V_{CB}[V]$ , COLLECTOR-BASE VOLTAGE

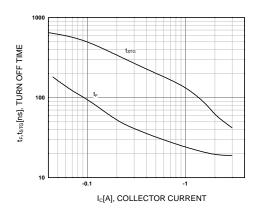


Figure 5. Turn Off Time

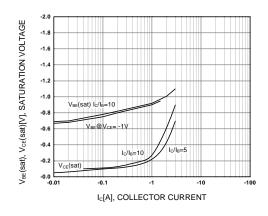


Figure 2. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

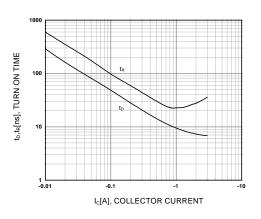


Figure 4. Turn On Time

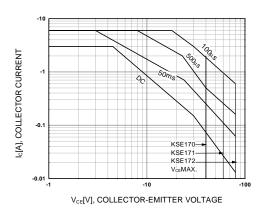


Figure 6. Safe Operating Area

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# Typical Characteristics (Continued)

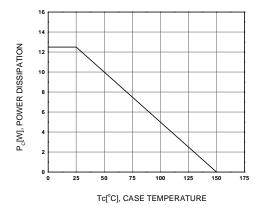
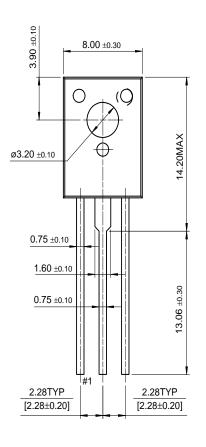
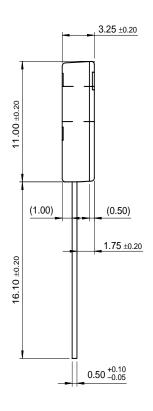


Figure 7. DC current Gain

# **Package Demensions**

TO-126







Dimensions in Millimeters

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